AMENDMENTS IN THE CLAIMS:

1. (Original) A method of growing a p-type nitride semiconductor material by molecular beam epitaxy, the method comprising supplying bis(cyclopentadienyl)magnesium (Cp_2Mg) during the growth process.

2. (Currently Amended) A method as claimed in claim 1, wherein the nitride semiconductor material is p-type (Ga,Al)N.

3. (Currently Amended) A method as claimed in claim 1, ~~and~~ comprising supplying ammonia gas during the growth process.

4. (Currently Amended) A method as claimed in claim 1, ~~and~~ comprising supplying ammonia gas, gallium and Cp_2Mg to a growth chamber, thereby to grow a layer of p-type GaN.

5. (Currently Amended) A method as claimed in claim 1, ~~and~~ comprising supplying ammonia gas, aluminium, gallium and Cp_2Mg to a growth chamber, thereby to grow a layer of p-type AlGaN.

6. (Currently Amended) A method as claimed in 1, ~~and~~ comprising changing the supply rate of Cp_2Mg during the growth of the nitride semiconductor material.

7. (Cancelled)

8. (Currently Amended) A method as claimed in claim 1, wherein the growth process is carried out at a temperature of at least 800°C.

9. (Currently Amended) A method as claimed in claim 1, wherein the growth process is carried out at a temperature of at least 850°C.

10. (Currently Amended) A method as claimed in claim 1, wherein the growth process is carried out at a temperature of at least 920°C.

11. (Currently Amended) A method as claimed in claim 1, wherein the growth process is carried out at a temperature of at least 950°C.

12. (Currently Amended) A method as claimed in claim 1, wherein the growth process is carried out at a temperature of 960°C or below.

13. (Currently Amended) A method as claimed in claim 1, ~~and~~ comprising supplying Cp_2Mg at a beam equivalent pressure of at least 1×10^{-9} mbar.

14. (Currently Amended) A method as claimed in claim 1, ~~and~~ comprising supplying Cp_2Mg at a beam equivalent pressure of at least 3×10^{-9} mbar.

15. (Currently Amended) A method as claimed in claim 1, ~~and~~ comprising supplying Cp_2Mg at a beam equivalent pressure of 1×10^{-7} mbar or below.

16. (Currently Amended) A method as claimed in claim 1, ~~and~~ comprising supplying Cp_2Mg at a beam equivalent pressure of 1.5×10^{-8} mbar or below.

17. (Currently Amended) A method as claimed in claim 4, ~~and~~ comprising supplying elemental gallium at a beam equivalent pressure of at least 1×10^{-8} mbar.

18. (Currently Amended) A method as claimed in claim 4, ~~and~~ comprising supplying elemental gallium at a beam equivalent pressure of 1×10^{-5} mbar or below.

19. (Currently Amended) A method as claimed in claim 5, ~~and~~ comprising supplying elemental gallium and elemental aluminium at an overall beam equivalent pressure of at least 1×10^{-8} mbar.

20. (Currently Amended) A method as claimed in claim 5, ~~and~~ comprising supplying elemental gallium and elemental aluminium at an overall beam equivalent pressure of 1×10^{-5}mbar or below.

21. (Previously Presented) A p-type nitride semiconductor material grown by a method defined in claim 1.

22. (Previously Presented) A semiconductor device comprising a layer of a p-type nitride semiconductor material grown by a method defined in claim 1.

23. (Currently Amended) A semiconductor device as claimed in claim 22, wherein the layer of nitride semiconductor material is a layer of p-type (Ga,Al)N.